

Amendments to the Specification:

A. Please amend the title to:

--SELF ALIGNED METHOD OF FORMING A SEMICONDUCTOR
MEMORY ARRAY OF FLOATING GATE MEMORY CELLS WITH BURIED
BIT-LINE AND VERTICAL WORD LINE TRANSISTOR--

B. Please add to the first line of the specification the following priority claim information:

--This application is a divisional of U.S. Application No. 09/982,413, filed October 17, 2001.--